



YEA SHIN TECHNOLOGY CO., LTD

YSE3907WBC

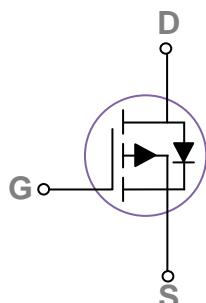
P-Channel Enhancement MOSFET
VDS= -30V, ID= -8.5A



Features

- $-30V, -8.5A, R_{DS(ON)} = 23m\Omega @ V_{GS} = -10V$
- *Fast switching*
- *Green Device Available*
- *Suit for -4.5V Gate Drive Applications*

PPAK2x3 Pin Configuration



Applications

- *MB / VGA / Vcore*
- *POL Applications*
- *Load Switch*
- *LED Application*

Absolute Maximum Rating $T_c=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_c=25^\circ C$)	-8.5	A
	Drain Current – Continuous ($T_c=100^\circ C$)	-5.3	A
I_{DM}	Drain Current – Pulsed ¹	-34	A
P_D	Power Dissipation ($T_c=25^\circ C$)	3	W
	Power Dissipation – Derate above $25^\circ C$	0.025	$W/^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	90	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	40	$^\circ C/W$

DEVICE CHARACTERISTICS

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Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$, $I_{\text{D}}=-250\mu\text{A}$	-30	---	---	V
$\Delta \text{BV}_{\text{DSS}}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_{\text{D}}=-1\text{mA}$	---	-0.03	---	$\text{V}/^\circ\text{C}$
I_{DSs}	Drain-Source Leakage Current	$V_{\text{DS}}=-30\text{V}$, $V_{\text{GS}}=0\text{V}$, $T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{\text{DS}}=-24\text{V}$, $V_{\text{GS}}=0\text{V}$, $T_J=125^\circ\text{C}$	---	---	-10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{\text{GS}}=\pm 20\text{V}$, $V_{\text{DS}}=0\text{V}$	---	---	± 20	μA

On Characteristics

$R_{\text{DS(on)}}$	Static Drain-source On-Resistance ²	$V_{\text{GS}}=-10\text{V}$, $I_{\text{D}}=-5\text{A}$	---	19	23	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}$, $I_{\text{D}}=-3\text{A}$	---	28	34	$\text{m}\Omega$
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{GS}}=V_{\text{DS}}$, $I_{\text{D}}=-250\mu\text{A}$	-1.2	-1.6	-2.5	V
			---	4	---	$\text{mV}/^\circ\text{C}$
g_{fs}	Forward Transconductance	$V_{\text{DS}}=-10\text{V}$, $I_{\text{D}}=-3\text{A}$	---	6.8	---	S

Dynamic and Switching Characteristics

Q_g	Total Gate Charge ^{2,3}	$V_{\text{DS}}=-15\text{V}$, $V_{\text{GS}}=-4.5\text{V}$, $I_{\text{D}}=-5\text{A}$	---	11	17	nC
Q_{gs}	Gate-Source Charge ^{2,3}		---	3.4	6	
Q_{gd}	Gate-Drain Charge ^{2,3}		---	4.2	8	
$T_{\text{d(on)}}$	Turn-On Delay Time ^{2,3}	$V_{\text{DD}}=-15\text{V}$, $V_{\text{GS}}=-10\text{V}$, $R_{\text{G}}=6\Omega$, $I_{\text{D}}=-1\text{A}$	---	5.8	11	ns
T_r	Rise Time ^{2,3}		---	18.8	36	
$T_{\text{d(off)}}$	Turn-On Delay Time ^{2,3}		---	46.9	90	
T_f	Fall Time ^{2,3}		---	12.3	23	
C_{iss}	Input Capacitance		---	1250	2500	pF
C_{oss}	Output Capacitance	$V_{\text{DS}}=-15\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	---	160	320	
C_{rss}	Reverse Transfer Capacitance		---	90	180	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_s	Continuous Source Current	$V_G=V_D=0\text{V}$, Force Current	---	---	-8.5	A
I_{SM}	Pulsed Source Current ²		---	---	-17	A
V_{SD}	Diode Forward Voltage ²	$V_{\text{GS}}=0\text{V}$, $I_{\text{S}}=-1\text{A}$, $T_J=25^\circ\text{C}$	---	---	-1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
3. Essentially independent of operating temperature.

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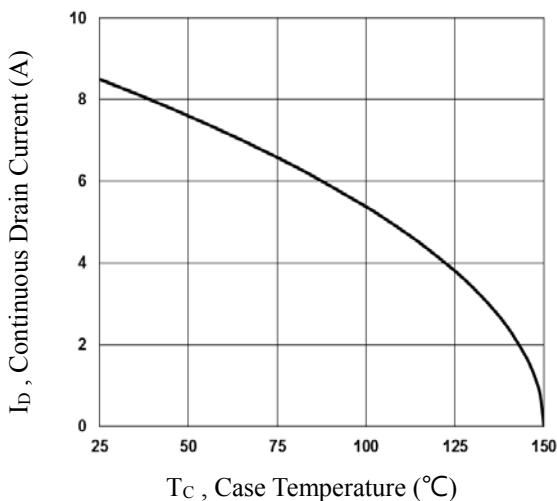


Fig.1 Continuous Drain Current vs. T_C

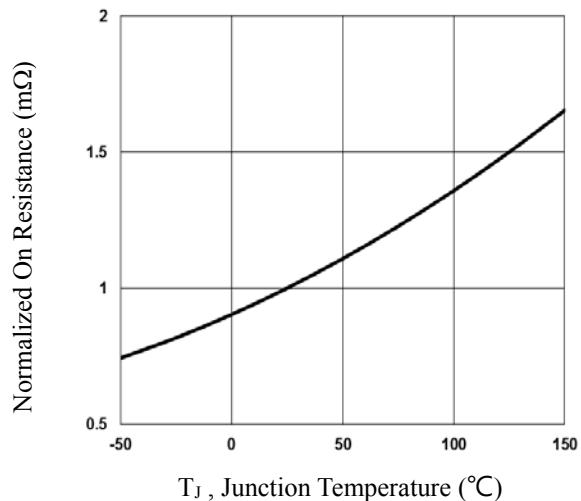


Fig.2 Normalized RDS(on) vs. T_J

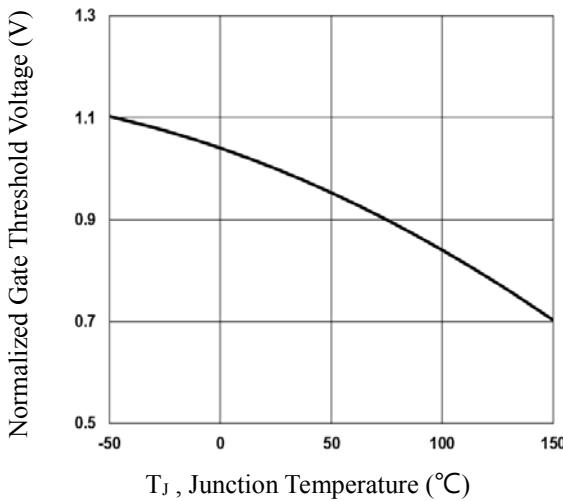


Fig.3 Normalized V_{th} vs. T_J

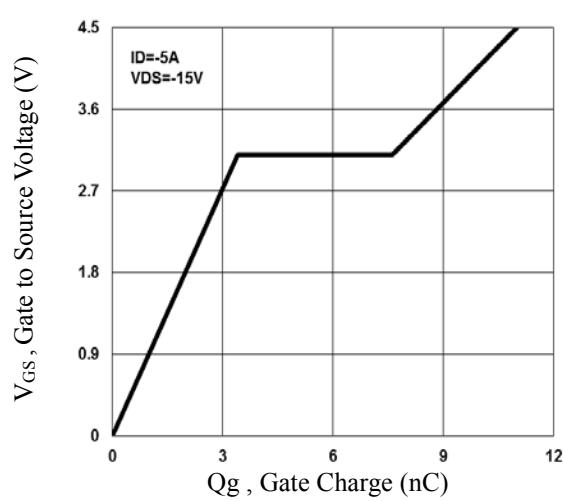


Fig.4 Gate Charge Waveform

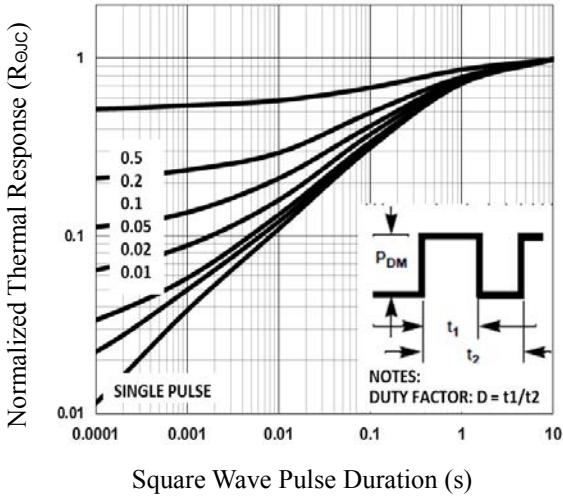


Fig.5 Normalized Transient Response

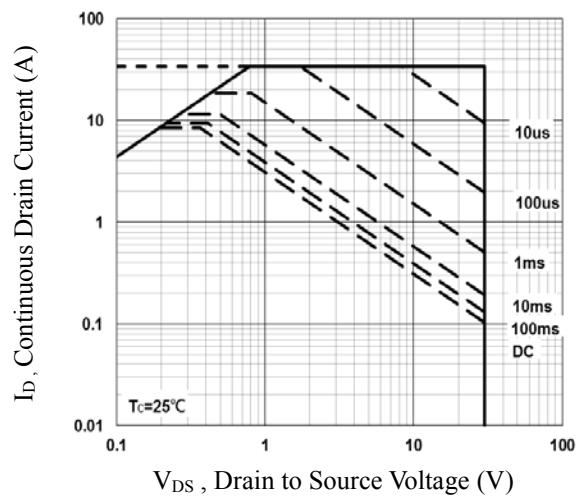


Fig.6 Maximum Safe Operation Area

DEVICE CHARACTERISTICS

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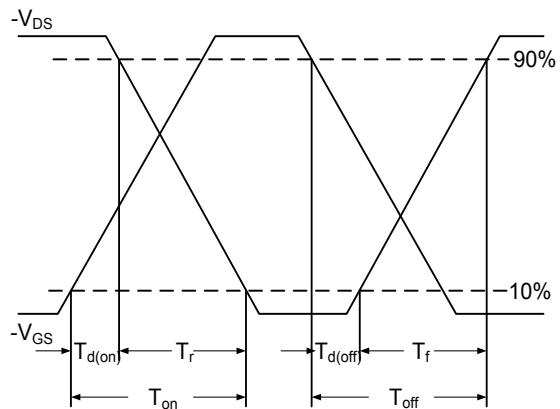


Fig.7 Switching Time Waveform

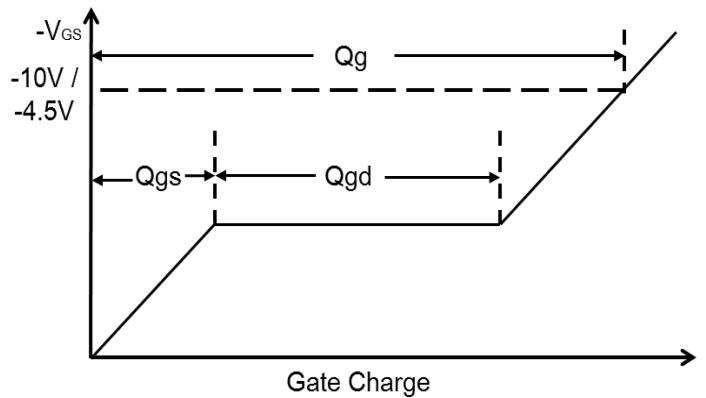
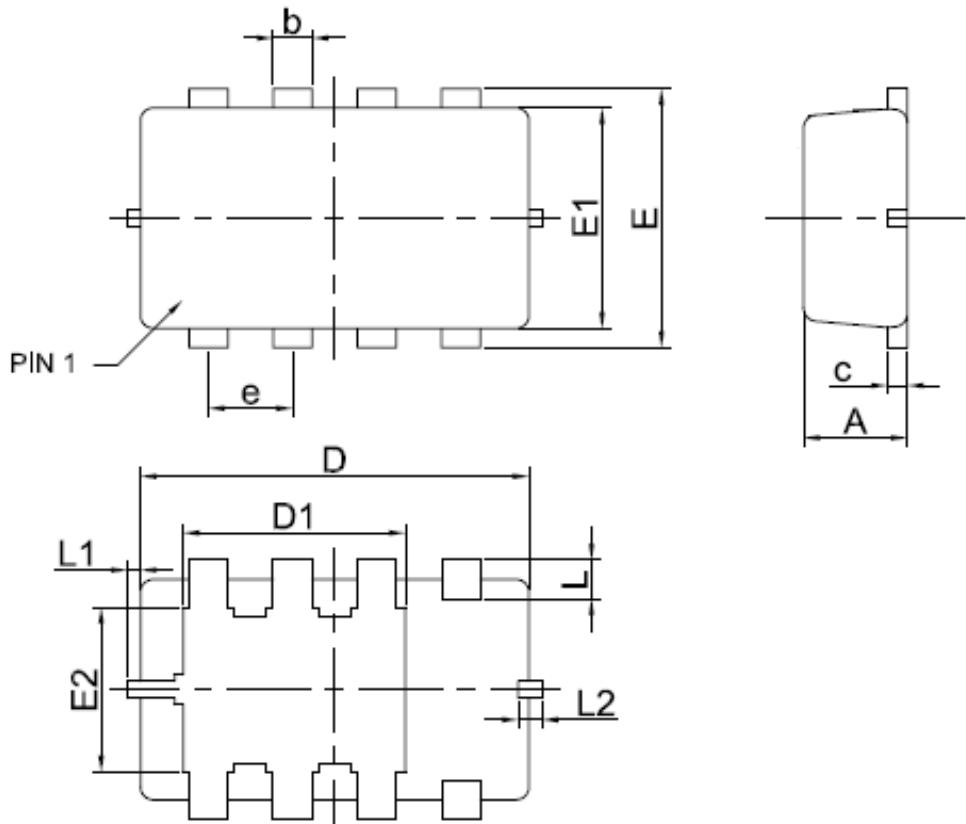


Fig.8 EAS Waveform

PACKAGE OUTLINE & DIMENSIONS

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PPAK2x3 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	0.900	0.700	0.035	0.028
b	0.350	0.240	0.014	0.009
c	0.200	0.080	0.008	0.003
D	3.100	2.900	0.122	0.114
D1	1.720	1.520	0.068	0.060
E	2.100	1.900	0.083	0.075
E1	1.800	1.600	0.071	0.063
E2	1.270	1.070	0.050	0.042
e	0.65BSC		0.026BSC	
L	0.400	0.200	0.016	0.008
L1	0.100	0.000	0.004	0.000
L2	0.184	-	0.007	-